

## 54F/74F10 Triple 3-Input NAND Gate

#### **General Description**

This device contains three independent gates, each of which performs the logic NAND function.

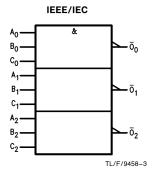
Commercial	Military	Package Number	Package Description
74F10PC		N14A	14-Lead (0.300" Wide) Molded Dual-In-Line
	54F10DM (Note 2)	J14A	14-Lead Ceramic Dual-In-Line
74F10SC (Note 1)		M14A	14-Lead (0.150" Wide) Molded Small Outline, JEDEC
74F10SJ (Note 1)		M14D	14-Lead (0.300" Wide) Molded Small Outline, EIAJ
	54F10FM (Note 2)	W14B	14-Lead Cerpack
	54F10LM (Note 2)	E20A	20-Lead Ceramic Leadless Chip Carrier, Type C

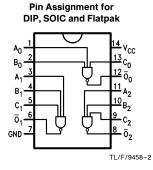
Note 1: Devices also available in 13" reel. Use suffix = SCX and SJX.

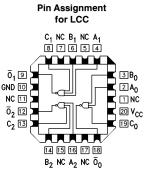
Note 2: Military grade device with environmental and burn-in processing. Use suffix = DMQB, FMQB and LMQB.

#### **Logic Symbol**

#### **Connection Diagrams**







TL/F/9458-1

#### **Unit Loading/Fan Out**

		54F/74F				
Pin Names	Description	U.L. HIGH/LOW	Input I <sub>IH</sub> /I <sub>IL</sub> Output I <sub>OH</sub> /I <sub>OL</sub>			
$A_n, B_n, C_n$ $\overline{O}_n$	Inputs Outputs	1.0/1.0 50/33.3	20 μA/ – 0.6 mA – 1 mA/20 mA			

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#### **Absolute Maximum Ratings** (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

 $\begin{array}{lll} \mbox{Storage Temperature} & -65^{\circ}\mbox{C to} + 150^{\circ}\mbox{C} \\ \mbox{Ambient Temperature under Bias} & -55^{\circ}\mbox{C to} + 125^{\circ}\mbox{C} \\ \mbox{Junction Temperature under Bias} & -55^{\circ}\mbox{C to} + 175^{\circ}\mbox{C} \\ \mbox{Plastic} & -55^{\circ}\mbox{C to} + 150^{\circ}\mbox{C} \\ \end{array}$ 

V<sub>CC</sub> Pin Potential to

Voltage Applied to Output

in HIGH State (with  $V_{CC} = 0V$ )

 $\begin{array}{ll} \mbox{Standard Output} & -0.5\mbox{V to V}_{\mbox{CC}} \\ \mbox{TRI-STATE} \mbox{$^{\circ}$ Output} & -0.5\mbox{V to } +5.5\mbox{V} \end{array}$ 

Current Applied to Output

in LOW State (Max) twice the rated I<sub>OL</sub> (mA)

**Note 1:** Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

# Recommended Operating Conditions

Free Air Ambient Temperature

Supply Voltage

Military + 4.5V to + 5.5V Commercial + 4.5V to + 5.5V

#### **DC Electrical Characteristics**

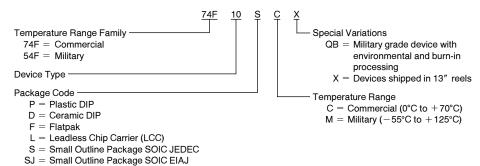
Symbol	Parameter		54F/74F			Units	v <sub>cc</sub>	Conditions	
Symbol			Min	Тур	Max	Oilles	VCC	Conditions	
V <sub>IH</sub>	Input HIGH Voltage		2.0			V		Recognized as a HIGH Signal	
$V_{IL}$	Input LOW Voltage				0.8	V		Recognized as a LOW Signal	
$V_{CD}$	Input Clamp Diode Voltage				-1.2	V	Min	$I_{\text{IN}} = -18  \text{mA}$	
V <sub>OH</sub>	Output HIGH Voltage	54F 10% V <sub>CC</sub> 74F 10% V <sub>CC</sub> 74F 5% V <sub>CC</sub>	2.5 2.5 2.7			V	Min	$I_{OH} = -1 \text{ mA}$ $I_{OH} = -1 \text{ mA}$ $I_{OH} = -1 \text{ mA}$	
V <sub>OL</sub>	Output LOW Voltage	54F 10% V <sub>CC</sub> 74F 10% V <sub>CC</sub>			0.5 0.5	٧	Min	I <sub>OL</sub> = 20 mA I <sub>OL</sub> = 20 mA	
I <sub>IH</sub>	Input HIGH Current	54F 74F			20.0 5.0	μΑ	Max	V <sub>IN</sub> = 2.7V	
I <sub>BVI</sub>	Input HIGH Current Breakdown Test	54F 74F			100 7.0	μΑ	Max	V <sub>IN</sub> = 7.0V	
I <sub>CEX</sub>	Output HIGH Leakage Current	54F 74F			250 50	μΑ	Max	$V_{OUT} = V_{CC}$	
V <sub>ID</sub>	Input Leakage Test	74F	4.75			٧	0.0	$I_{\text{ID}} = 1.9 \mu\text{A}$ All other pins grounded	
I <sub>OD</sub>	Output Leakage Circuit Current	74F			3.75	μΑ	0.0	V <sub>IOD</sub> = 150 mV All other pins grounded	
I <sub>IL</sub>	Input LOW Current				-0.6	mA	Max	$V_{IN} = 0.5V$	
los	Output Short-Circuit Current		-60		-150	mA	Max	V <sub>OUT</sub> = 0V	
Іссн	Power Supply Current			1.4	2.1	mA	Max	V <sub>O</sub> = HIGH	
ICCL	Power Supply Current		5.1	7.7	mA	Max	$V_O = LOW$		

#### **AC Electrical Characteristics**

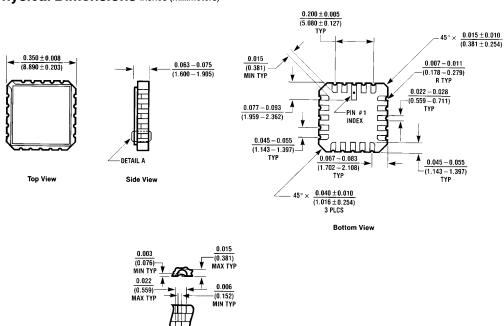
		$ \begin{array}{c} {\it T_{A}} = +25^{\circ}{\it C} \\ {\it V_{CC}} = +5.0{\it V} \\ {\it C_{L}} = 50{\it pF} \end{array} $			54F  T <sub>A</sub> , V <sub>CC</sub> = Mil  C <sub>L</sub> = 50 pF		$74F$ $T_{A}, V_{CC} = Com$ $C_{L} = 50 \text{ pF}$		Units
Symbol	Parameter								
		Min	Тур	Max	Min	Max	Min	Max	
t <sub>PLH</sub>	Propagation Delay	2.4	3.7	5.0	2.0	7.0	2.4	6.0	ne
t <sub>PHL</sub>	$A_n$ , $B_n$ , $C_n$ to $\overline{O}_n$	1.5	3.2	4.3	1.5	6.5	1.5	5.3	ns

### **Ordering Information**

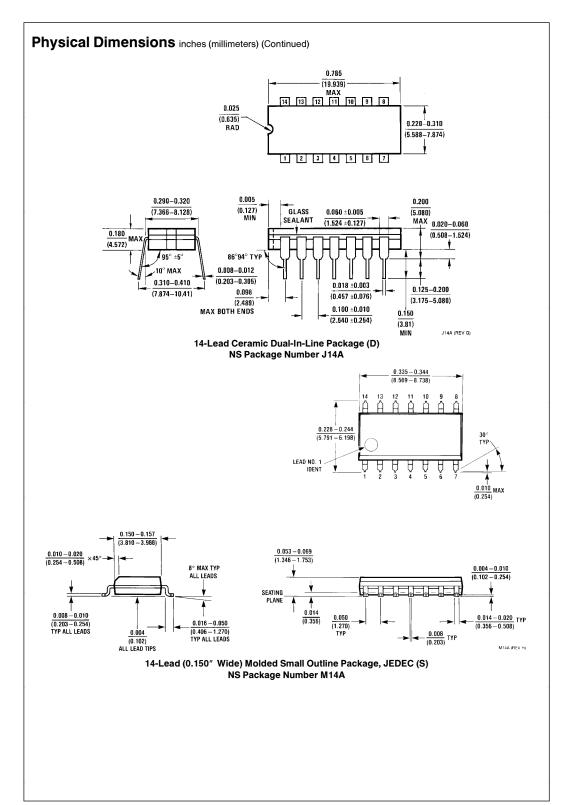
The device number is used to form part of a simplified purchasing code where the package type and temperature range are defined as follows:

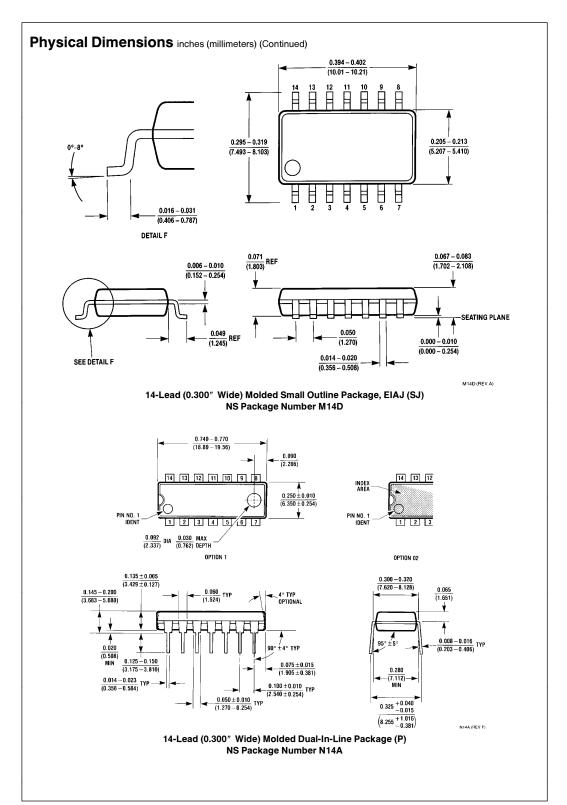


#### Physical Dimensions inches (millimeters)

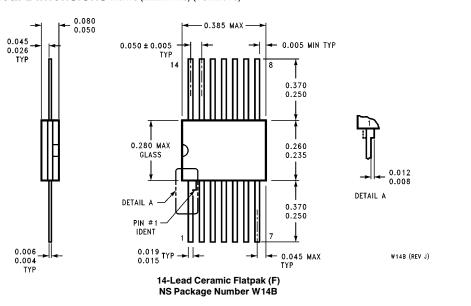


20-Lead Ceramic Leadless Chip Carrier (L) NS Package Number E20A E20A (REV D)





#### Physical Dimensions inches (millimeters) (Continued)



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